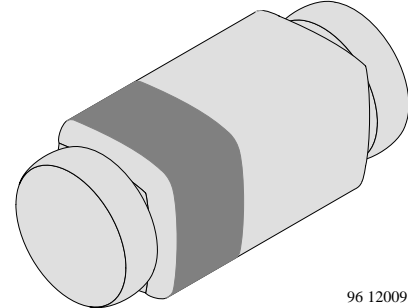


Switching Diode

Features

- Silicon Epitaxial Planar Diodes



96 12009

Applications

General purposes

Order Instruction

Type	Type Differentiation	Ordering Code	Remarks
BAV200	$V_{RRM} = 60\text{ V}$	BAV200-GS08	Tape and Reel
BAV201	$V_{RRM} = 120\text{ V}$	BAV201-GS08	Tape and Reel
BAV202	$V_{RRM} = 200\text{ V}$	BAV202-GS08	Tape and Reel
BAV203	$V_{RRM} = 250\text{ V}$	BAV203-GS08	Tape and Reel

Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Peak reverse voltage		BAV200	V_{RRM}	60	V
		BAV201		120	V
		BAV202		200	V
		BAV203		250	V
Reverse voltage		BAV200	V_R	50	V
		BAV201		100	V
		BAV202		150	V
		BAV203		200	V
Forward current			I_F	250	mA
Peak forward surge current	$t_p=1\text{s}, T_j=25^\circ\text{C}$		I_{FSM}	1	A
Forward peak current	$f=50\text{Hz}$		I_{FM}	625	mA
Junction temperature			T_j	175	$^\circ\text{C}$
Storage temperature range			T_{stg}	-65...+175	$^\circ\text{C}$

Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50 mmx50 mmx1.6 mm	R_{thJA}	500	K/W

Electrical Characteristics

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=100\text{mA}$		V_F			1	V
Reverse current	$V_R=50\text{ V}$	BAV200	I_R			100	nA
	$V_R=100\text{ V}$	BAV201	I_R			100	nA
	$V_R=150\text{ V}$	BAV202	I_R			100	nA
	$V_R=200\text{ V}$	BAV203	I_R			100	nA
	$T_j=100^\circ\text{C}, V_R=50\text{ V}$	BAV200	I_R			15	μA
	$T_j=100^\circ\text{C}, V_R=100\text{ V}$	BAV201	I_R			15	μA
	$T_j=100^\circ\text{C}, V_R=150\text{ V}$	BAV202	I_R			15	μA
	$T_j=100^\circ\text{C}, V_R=200\text{ V}$	BAV203	I_R			15	μA
Breakdown voltage	$I_R=100\mu\text{A}, t_p/T=0.01, t_p=0.3\text{ms}$	BAV200	$V_{(BR)}$	60			V
		BAV201	$V_{(BR)}$	120			V
		BAV202	$V_{(BR)}$	200			V
		BAV203	$V_{(BR)}$	250			V
Diode capacitance	$V_R=0, f=1\text{MHz}$		C_D		1.5		pF
Differential forward resistance	$I_F=10\text{mA}$		r_f		5		Ω
Reverse recovery time	$I_F=I_R=30\text{mA}, i_R=3\text{mA}, R_L=100\Omega$		t_{rr}			50	ns

Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

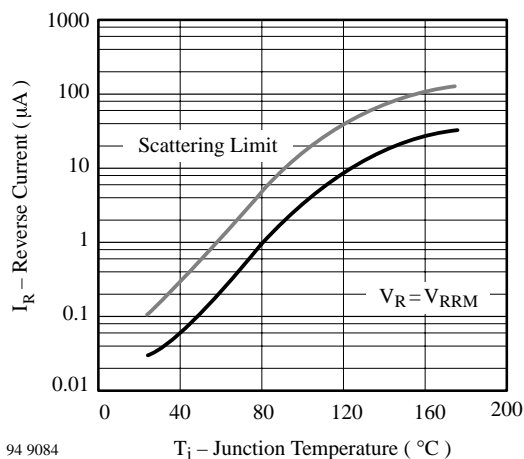


Figure 1. Reverse Current vs. Junction Temperature

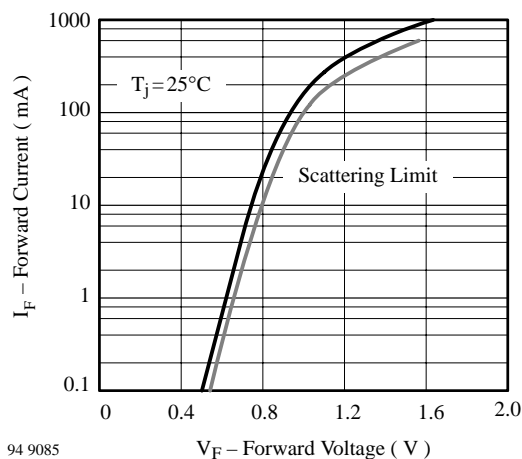


Figure 2. Forward Current vs. Forward Voltage

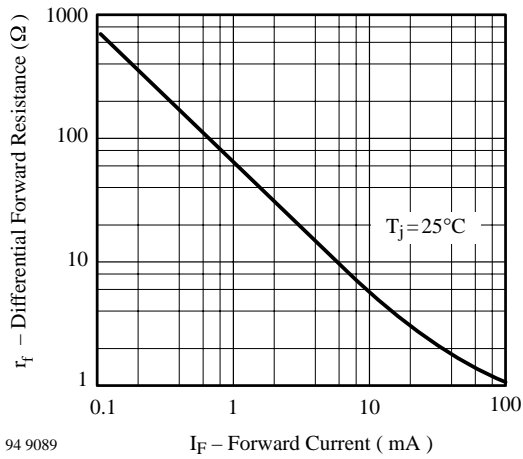
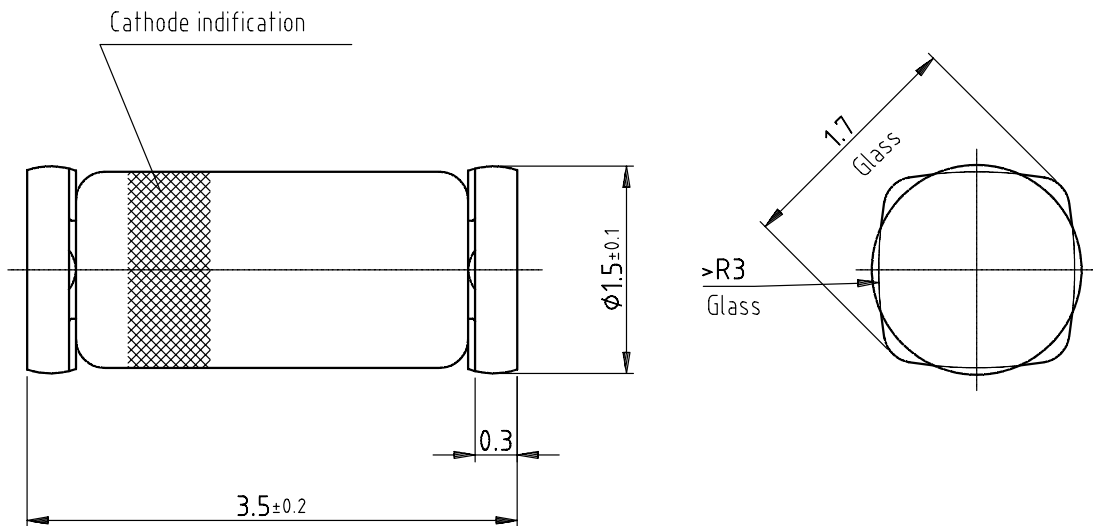
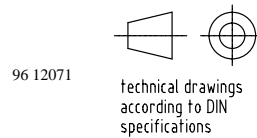


Figure 3. Differential Forward Resistance vs. Forward Current

Dimensions in mm



Glass case
 Quadro MELF / SOD80
 similar to JEDEC 213 AA



96 12071

technical drawings
 according to DIN
 specifications

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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